Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C.

Supporting Information

Mimicking the competitive and cooperative behaviors with multi-terminal synaptic memtransistors

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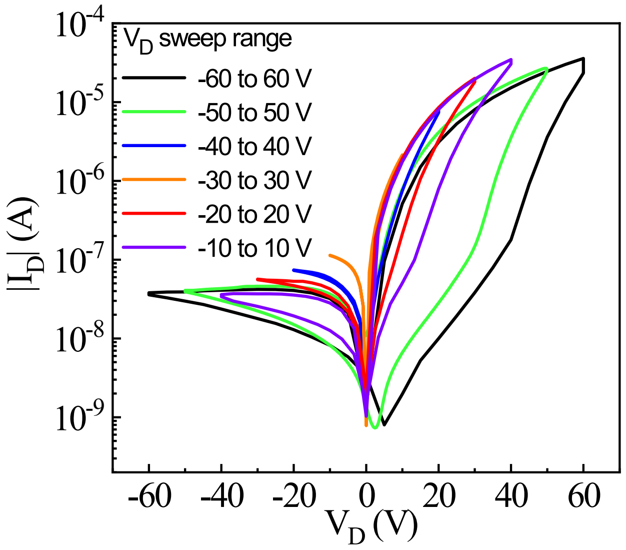
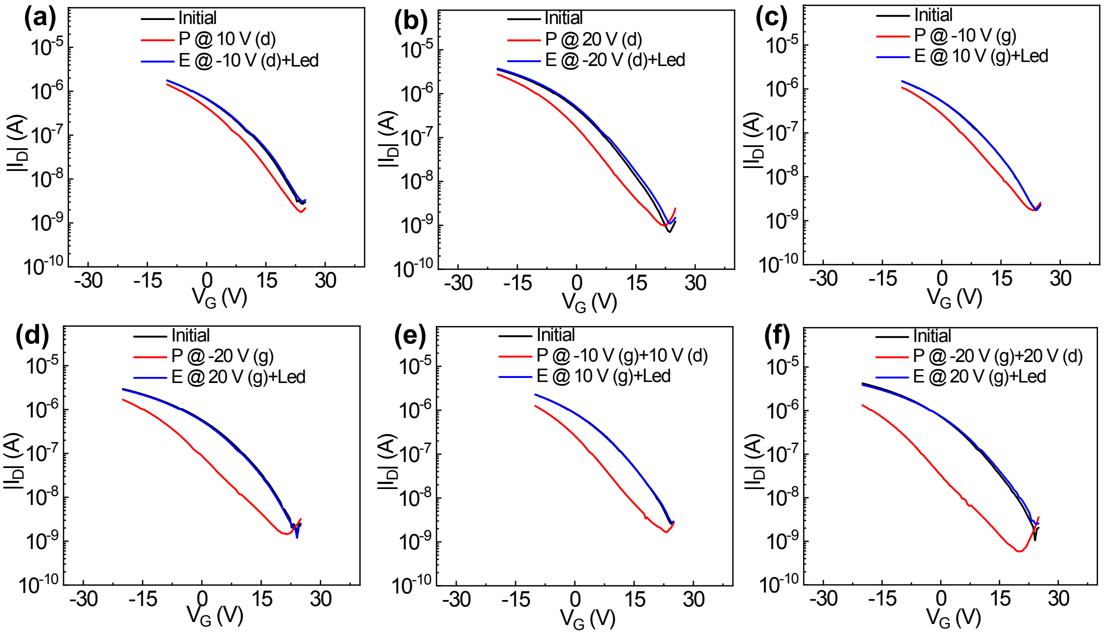


Fugure S1. I_D-V_D curves of memtransistor with different scanning ranges of V_D.



Fugure S2. The memory windows with different types of holes injected by the drain voltage and gate voltage: (a) 10 V (V_D); (b) 20 V (V_D); (c) -10 V (V_G); (d) -20 V (V_G); (e) -10 V (V_G) + 10 V (V_D) and (f) -20 V (V_G) + 20 V